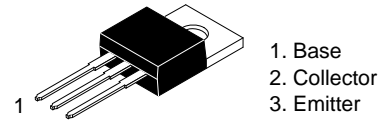


NPN Epitaxial Silicon Transistor

KSD526

TO-220-3LD
CASE 340AT

Features

- Complement to KSB596
- This is a Pb-Free Device

Applications

- Power Amplifier Applications

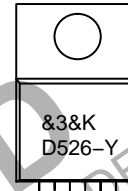
ABSOLUTE MAXIMUM RATINGS* ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	4	A
I_B	Base Current	0.4	A
P_C	Collector Dissipation ($T_C = 25^\circ\text{C}$)	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 ~ 150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

MARKING DIAGRAM



&3 = Date Code
&K = Lot Traceability Code
D526-Y = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
KSD526Y	TO-220-3LD (Pb-Free)	1200 Units / Bulk Bag
KSD526YTU	TO-220-3LD (Pb-Free)	1000 Units / Tube

KSD526

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
I _{CBO}	Collector Cut-off Current	V _{CB} = 80 V, I _E = 0			30	μA
I _{EBO}	Emitter Cut-off Current	V _{EB} = 5 V, I _C = 0			100	μA
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 50 mA, I _B = 0	80			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 10 mA, I _C = 0	5			V
h _{FE}	DC Current Gain	V _{CE} = 5 V, I _C = 0.5 A V _{CE} = 5 V, I _C = 3 A	40 15	50	240	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3 A, I _B = 0.3 A		0.45	1.5	V
V _{BE(on)}	Base-Emitter On Voltage	V _{CE} = 5 V, I _C = 3 A		1	1.5	V
f _T	Current Gain – Bandwidth Product	V _{CE} = 5 V, I _C = 0.5 A	3	8		MHz
C _{cb}	Collector Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz		90		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

h_{FE} CLASSIFICATION

Classification	R	O	Y
h _{FE}	40 ~ 80	70 ~ 140	120 ~ 240

TYPICAL CHARACTERISTICS

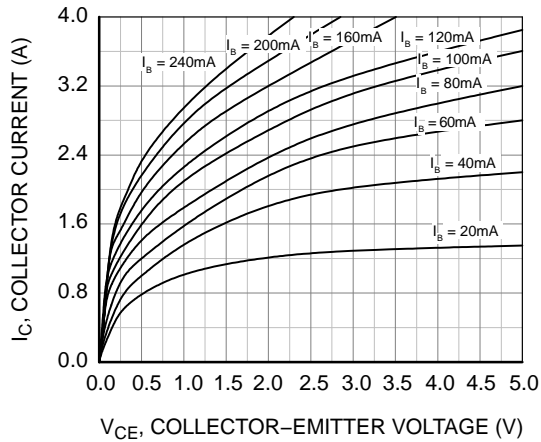


Figure 1. Static Characteristic

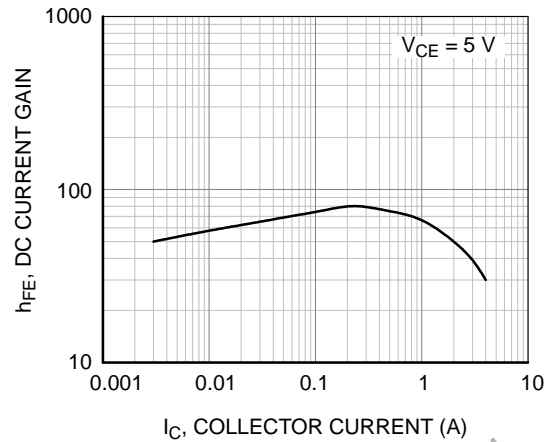


Figure 2. DC Current Gain

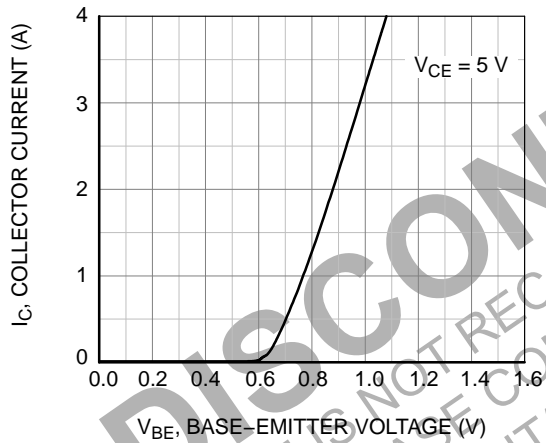


Figure 3. Base-Emitter On Voltage

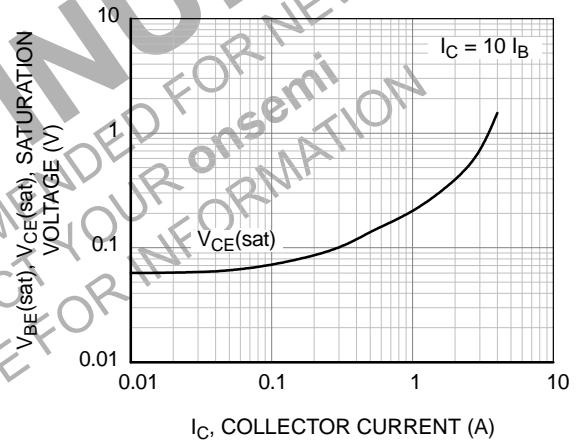


Figure 4. Collector-Emitter Saturation Voltage

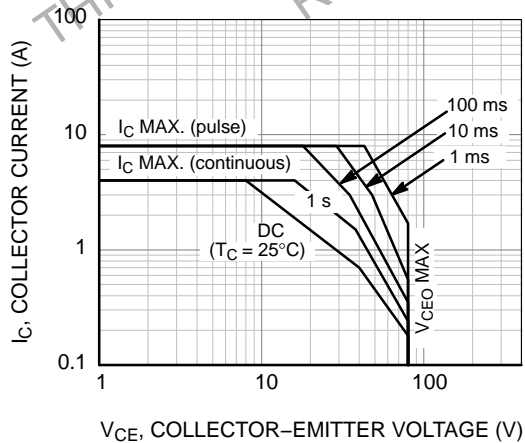


Figure 5. Safe Operating Area

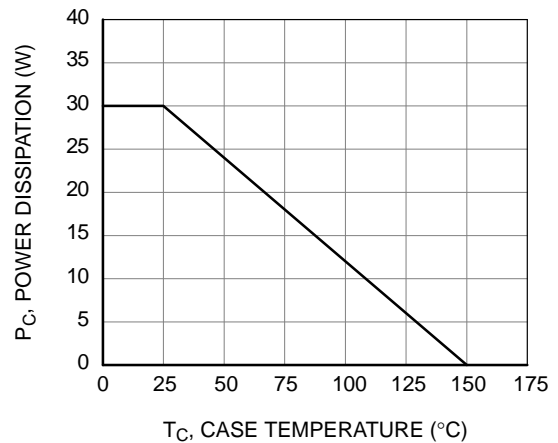
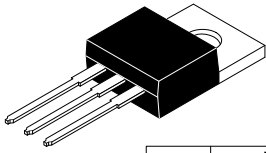


Figure 6. Power Derating



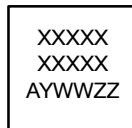
TO-220-3LD
CASE 340AT
ISSUE B

DATE 08 AUG 2022

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.00	--	4.70
A1	SEE NOTE "F"		
A2	2.10	--	2.85
b	0.55	--	1.00
b2	1.10	--	1.62
b4	1.42	--	1.62
c	0.36	--	0.60
D	13.90	--	16.30
D1	8.13	--	9.40
D2	11.50	--	14.30
D3	15.42	--	16.51
E	9.65	--	10.67
E1	7.59	--	8.65
e	2.40	--	2.67
H1	6.06	--	6.69
L	12.70	--	14.04
L1	2.70	--	4.10
P	3.50	--	4.00
Q	2.50	--	3.40
z	2.13 REF		
z1	2.06 REF		
θ	3°	--	5°

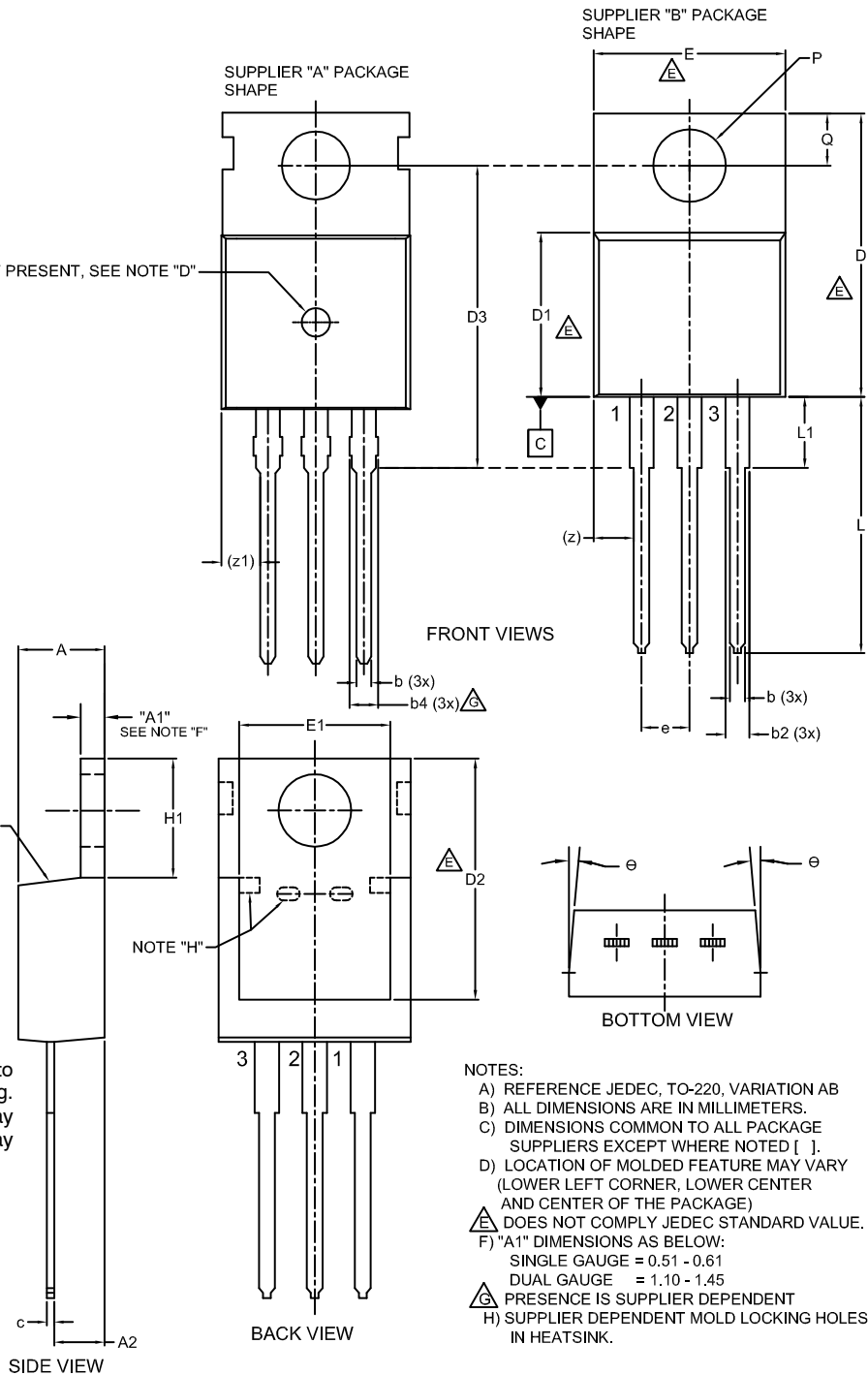
IF PRESENT, SEE NOTE "D"

GENERIC
MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



NOTES:

- A) REFERENCE JEDEC, TO-220, VARIATION AB
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [].
- D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
- E) DOES NOT COMPLY JEDEC STANDARD VALUE.
- F) "A1" DIMENSIONS AS BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.10 - 1.45
- G) PRESENCE IS SUPPLIER DEPENDENT
- H) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

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DESCRIPTION:	TO-220-3LD	PAGE 1 OF 1

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